



SEMIPONT® 2

Power Bridge Rectifiers

SKB 60

Features

- Robust plastic case with screw terminals
- Large, isolated base plate
- Blocking voltage to 1600 V
- High surge currents
- Single phase bridge rectifier
- Easy chassis mounting
- UL recognized, file no. E 63 532

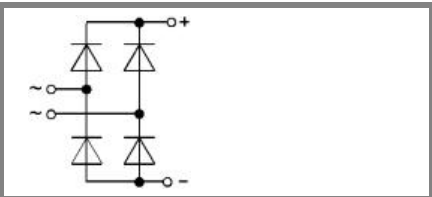
Typical Applications

- Single phase rectifiers for power supplies
- Input rectifiers for variable frequency drives
- Rectifiers for DC motor field supplies
- Battery charger rectifiers

1) Painted metal sheet of minimum
250 x 250 x 1 mm: $R_{th(c-a)} = 1,8 \text{ K/W}$

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 60 \text{ A}$ (full conduction) ($T_c = 88 \text{ }^\circ\text{C}$)
400	400	SKB 60/04
800	800	SKB 60/08
1200	1200	SKB 60/12
1400	1400	SKB 60/14
1600	1600	SKB 60/16

Symbol	Conditions	Values	Units
I_D	$T_c = 85 \text{ }^\circ\text{C}$	67	A
	inductive load		A
	$T_a = 45 \text{ }^\circ\text{C}$, chassis ¹⁾	20	A
	$T_a = 45 \text{ }^\circ\text{C}$; P13A/125 (P1A/120)	25 (44)	A
	$T_a = 35 \text{ }^\circ\text{C}$, P1A/200F	88	A
I_{FSM}	$T_{vj} = 25 \text{ }^\circ\text{C}$; 10 ms	1000	A
i^2t	$T_{vj} = 125 \text{ }^\circ\text{C}$; 10 ms	850	A
	$T_{vj} = 25 \text{ }^\circ\text{C}$; 8,3 ... 10 ms	5000	A ² s
	$T_{vj} = 125 \text{ }^\circ\text{C}$; 8,3 ... 10 ms	3600	A ² s
V_F	$T_{vj} = 25 \text{ }^\circ\text{C}$; $I_F = 150 \text{ A}$	max. 1,6	V
$V_{(TO)}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	max. 0,85	V
r_T	$T_{vj} = 125 \text{ }^\circ\text{C}$	max. 5	mΩ
I_{RD}	$T_{vj} = 25 \text{ }^\circ\text{C}$; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$	max. 0,5	mA
	$T_{vj} = 125 \text{ }^\circ\text{C}$; $V_{RD} = V_{RRM}$	2	mA
$R_{th(j-c)}$	per diode	1	K/W
	total	0,25	K/W
$R_{th(c-s)}$	total	0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 (3000)	V
M_s	to heatsink	5 ± 15 %	Nm
M_t	to terminals	5 ± 15 %	Nm
m		165	g
Case		G 17	



SKB

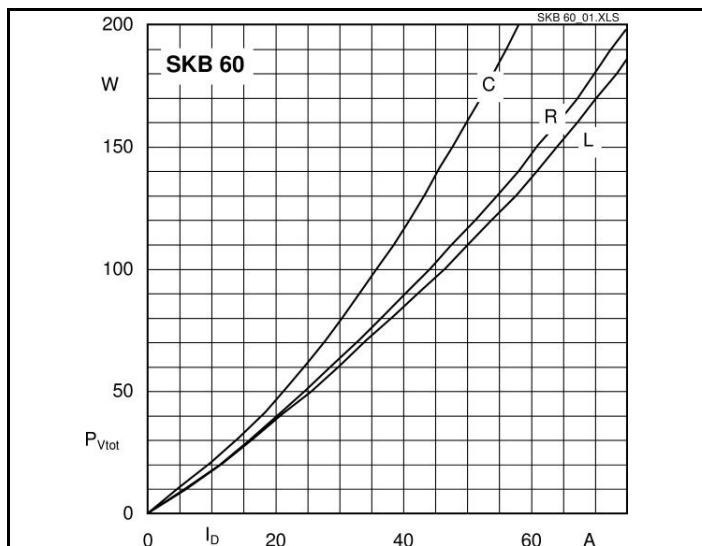


Fig. 3L Power dissipation vs. output current

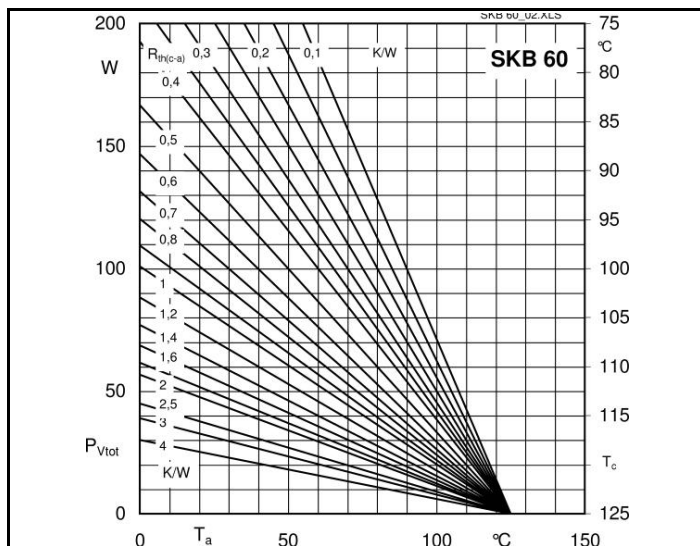


Fig. 3R Power dissipation vs. case temperature

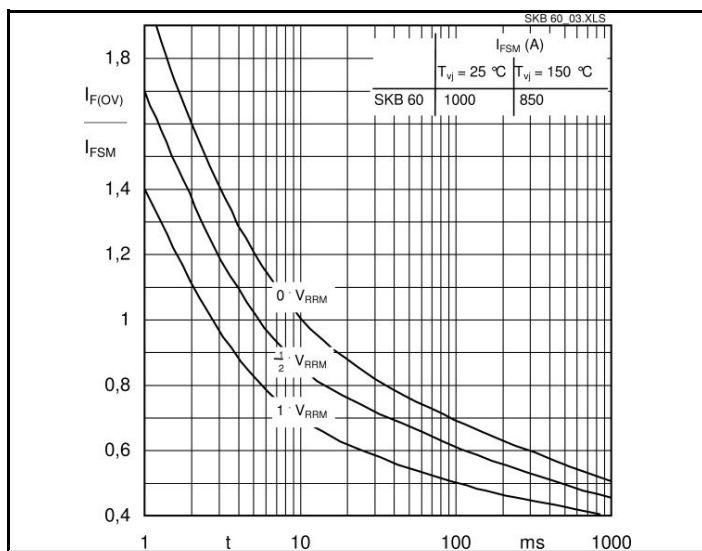


Fig. 6 Surge overload characteristics vs. time

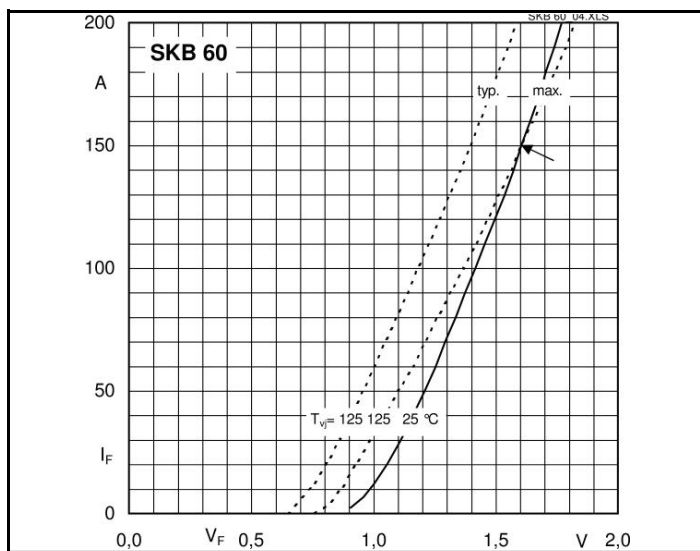


Fig. 9 Forward characteristics of a diode arm

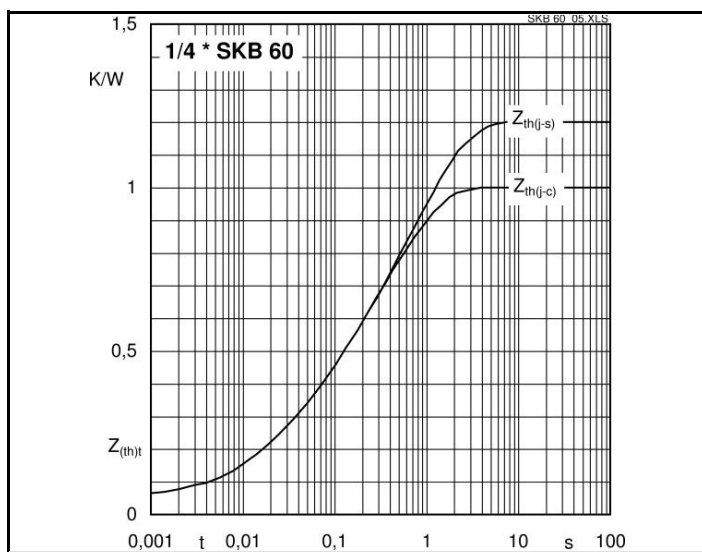
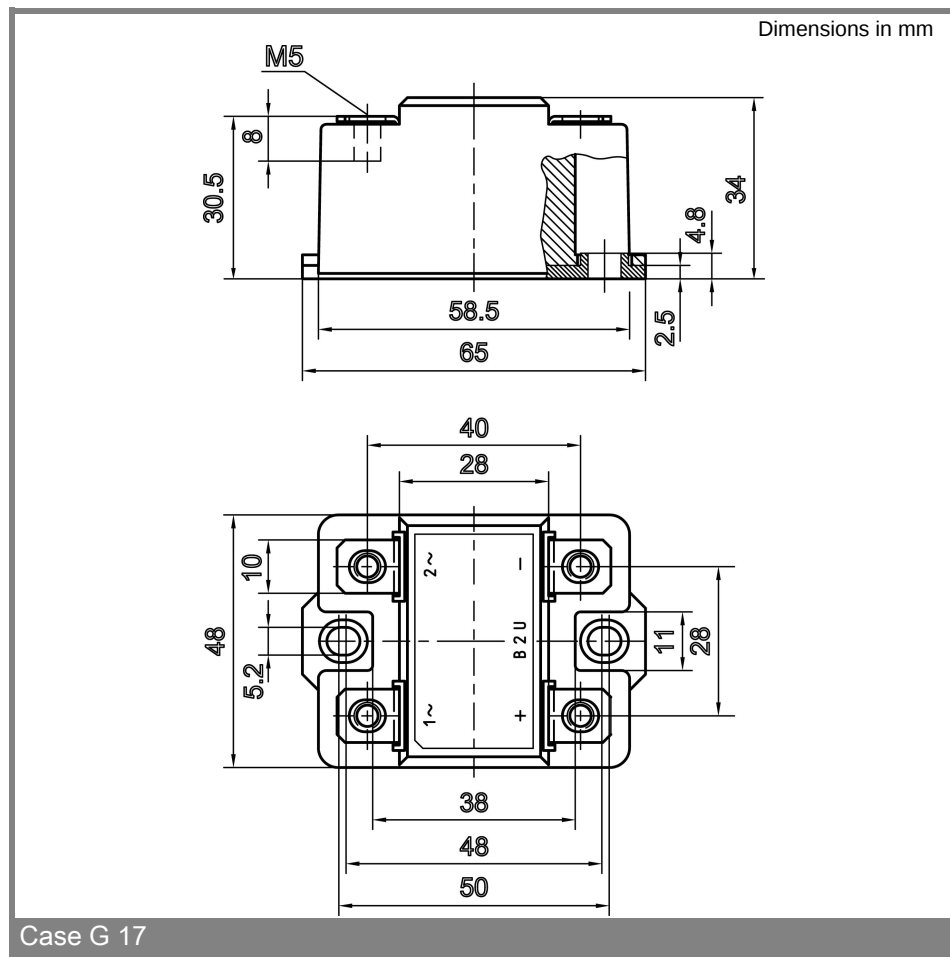


Fig. 12 Transient thermal impedance vs. time



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